

MGFC38V5964

5.9~6.4GHz BAND 6W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC38V5964 is an internally impedance-matched GaAs power FET especially designed for use in 5.9~6.4 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

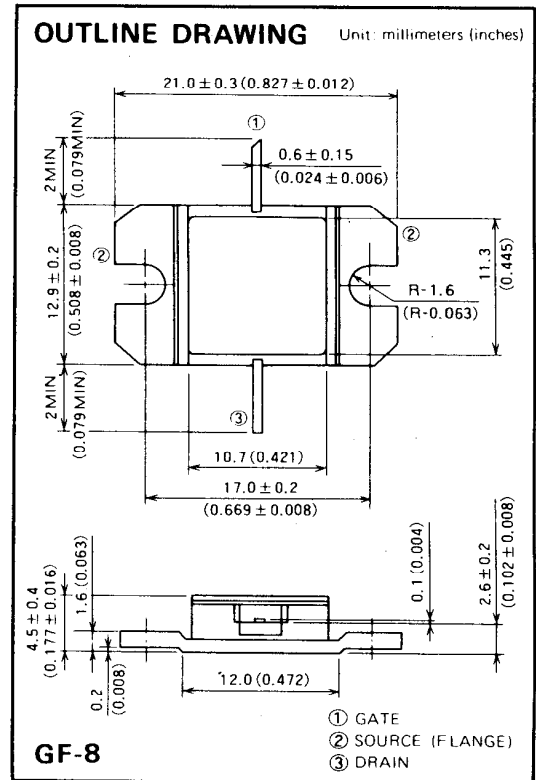
- Class A operation
- Internally matched to 50Ω system
- High output power
 $P_{1dB} = 6W$ (TYP) @ 5.9~6.4GHz
- High power gain
 $G_{LP} = 10dB$ (TYP) @ 5.9~6.4GHz
- High power added efficiency
 $\eta_{add} = 32%$ (TYP) @ 5.9~6.4GHz, P_{1dB}
- Hermetically sealed metal-ceramic package
- Low distortion [Item: -51]
 $IM_3 = -45$ dBc (TYP) @ $P_o = 27$ (dBm) S.C.L.

APPLICATION

- Item-01: 5.9~6.4GHz band power amplifier
- Item-51: Digital radio communication

QUALITY GRADE

- IG



ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

| Symbol | Parameter | Rating | Unit |
|------------------|----------------------------|------------|------|
| V _{GD0} | Gate to drain voltage | -15 | V |
| V _{GS0} | Gate to source voltage | -15 | V |
| I _D | Drain current | 5.0 | A |
| I _{GR} | Reverse gate current | -15 | mA |
| I _{GF} | Forward gate current | 31.5 | mA |
| P _T | Total power dissipation *1 | 30 | W |
| T _{ch} | Channel temperature | 175 | °C |
| T _{stg} | Storage temperature | -65 ~ +175 | °C |

*1: T_c = 25°C

RECOMMENDED BIAS CONDITIONS

- V_{DS} = 10V
- I_D = 1.8A
- R_g = 100Ω
- Refer to Bias Procedure

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

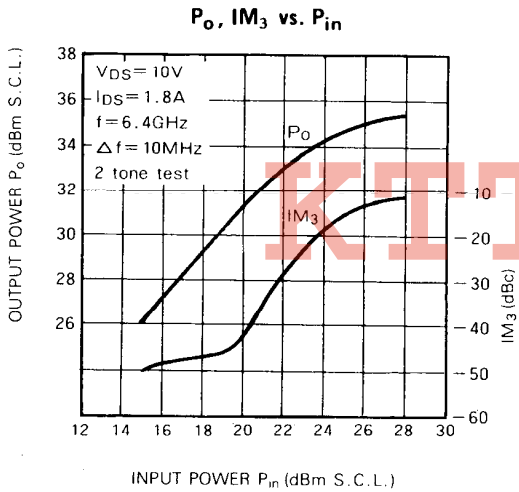
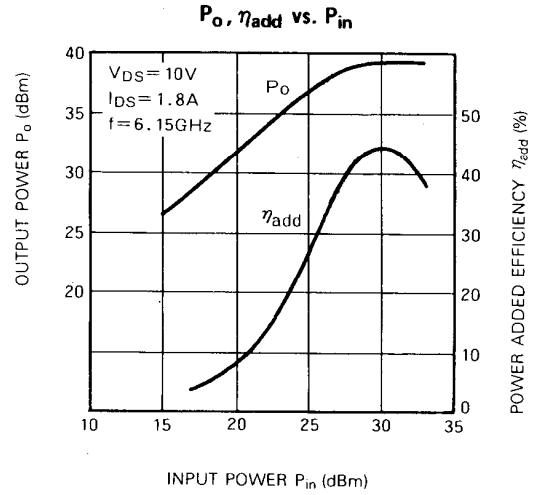
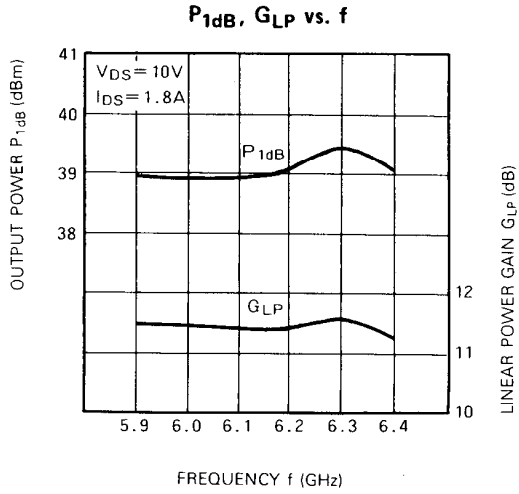
| Symbol | Parameter | Test conditions | Limits | | | Unit | |
|-----------------------|--------------------------------------|--|------------------------|------|------|------|------|
| | | | Min | Typ | Max | | |
| I _{DSS} | Saturated drain current | V _{DS} = 3V, V _{GS} = 0V | — | — | 5.0 | A | |
| g _m | Transconductance | V _{DS} = 3V, I _D = 1.5A | — | 2 | — | S | |
| V _{GS(off)} | Gate to source cut-off voltage | V _{DS} = 3V, I _D = 15mA | — | -3.5 | -5.0 | V | |
| P _{1dB} | Output power at 1dB gain compression | V _{DS} = 10V, I _D = 1.8A, f = 5.9~6.4GHz | 37 | 38 | — | dBm | |
| G _{LP} | Linear power gain | | 9 | 10 | — | dB | |
| I _D | Drain current | | — | 1.7 | — | A | |
| η _{add} | Power added efficiency | | — | 32 | — | % | |
| *IM ₃ | 3rd order IM distortion *1 | | -42 | -45 | — | dBc | |
| R _{th(ch-c)} | Thermal resistance *2 | | ΔV _f method | — | — | 5.0 | °C/W |

*1: Item-51, 2-tone test P_o = 27 dBm Single Carrier Level f = 6.4GHz Δf = 10 MHz.

*2: Channel to case

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TYPICAL CHARACTERISTICS (Ta=25°C)



S PARAMETERS (Ta=25°C, V_{DS}=10V, I_{DS}=1.8A)

| f (GHz) | S Parameters (TYP.) | | | | | | | |
|------------|---------------------|--------------|-----------------|--------------|-----------------|--------------|-----------------|--------------|
| | S ₁₁ | | S ₂₁ | | S ₁₂ | | S ₂₂ | |
| | Magn. | Angle (deg.) | Magn. | Angle (deg.) | Magn. | Angle (deg.) | Magn. | Angle (deg.) |
| 5.9 | 0.33 | -140 | 3.39 | 23 | 0.037 | -3 | 0.38 | -113 |
| 6.0 | 0.28 | -172 | 3.40 | 6 | 0.044 | -26 | 0.35 | -135 |
| 6.1 | 0.26 | 156 | 3.44 | -11 | 0.047 | -49 | 0.35 | -157 |
| 6.2 | 0.25 | 127 | 3.36 | -29 | 0.051 | -67 | 0.35 | -178 |
| 6.3 | 0.25 | 99 | 3.27 | -46 | 0.049 | -91 | 0.39 | 164 |
| 6.4 | 0.26 | 74 | 3.15 | -62 | 0.054 | -106 | 0.41 | 147 |

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